



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

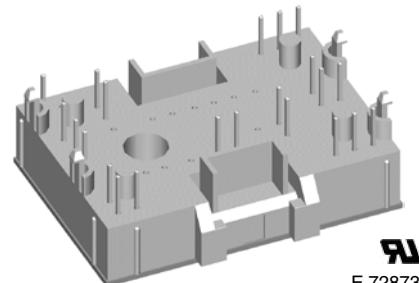
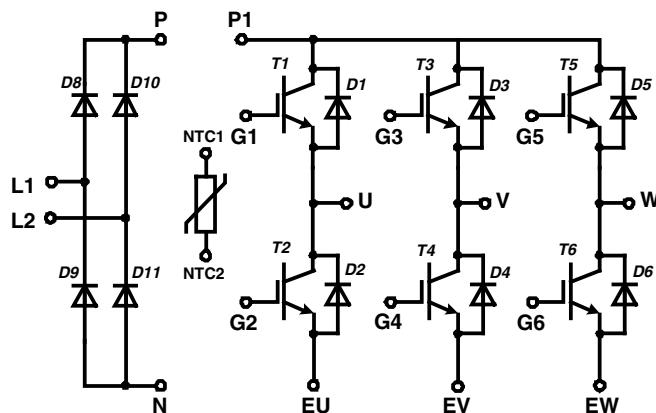
Converter - Inverter Module

NPT IGBT

Single Phase Rectifier	Three Phase Inverter
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 600 \text{ V}$
$I_{DAVM25} = 65 \text{ A}$	$I_{C25} = 23 \text{ A}$
$I_{FSM} = 550 \text{ A}$	$V_{CE(sat)} = 2.1 \text{ V}$

Part name (Marking on product)

MIAA15WD600TMH



E 72873

Pin configuration see outlines.

Features:

- High level of integration - only one power semiconductor module required for the whole drive
- Inverter with NPT IGBTs
 - low saturation voltage
 - positive temperature coefficient
 - fast switching
 - short tail current
- Epitaxial free wheeling diodes with hiperfast soft reverse recovery
- Temperature sense included

Application:

- AC motor drives
- Pumps, Fans
- Washing machines
- Air-conditioning system
- Inverter and power supplies

Package:

- "Mini" package
- Assembly height is 17 mm
- Insulated base plate
- Pins suitable for wave soldering and PCB mounting
- Assembly clips available
 - IXKU 5-505 screw clamp
 - IXRB 5-506 click clamp
- UL registered E72873

Output Inverter T1 - T6

Ratings

Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V_{CES}	collector emitter voltage	$T_{VJ} = 150^\circ\text{C}$			600	V
V_{GES}	max. DC gate voltage	continuous			± 20	V
V_{GEM}	max. transient collector gate voltage	transient			± 30	V
I_{C25}	collector current	$T_C = 25^\circ\text{C}$			23	A
I_{C80}		$T_C = 80^\circ\text{C}$			16	A
P_{tot}	total power dissipation	$T_C = 25^\circ\text{C}$			80	W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 15 \text{ A}; V_{GE} = 15 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$	2.1	2.5	V
			$T_{VJ} = 125^\circ\text{C}$	2.3		V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.4 \text{ A}; V_{GE} = V_{CE}$	$T_{VJ} = 25^\circ\text{C}$	4.5	5.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$		0.6	mA
			$T_{VJ} = 125^\circ\text{C}$		1.0	mA
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20 \text{ V}$			150	nA
C_{ies}	input capacitance	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$			700	pF
$Q_{G(on)}$	total gate charge	$V_{CE} = 300 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 15 \text{ A}$			57	nC
$t_{d(on)}$	turn-on delay time	$T_{VJ} = 25^\circ\text{C}$ $V_{CE} = 300 \text{ V}; I_C = 15 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 68 \Omega$			40	ns
t_r	current rise time				45	ns
$t_{d(off)}$	turn-off delay time				155	ns
t_f	current fall time				95	ns
E_{on}	turn-on energy per pulse				0.35	mJ
E_{off}	turn-off energy per pulse				0.27	mJ
$t_{d(on)}$	turn-on delay time	$T_{VJ} = 125^\circ\text{C}$ $V_{CE} = 300 \text{ V}; I_C = 15 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 68 \Omega$			40	ns
t_r	current rise time				45	ns
$t_{d(off)}$	turn-off delay time				160	ns
t_f	current fall time				120	ns
E_{on}	turn-on energy per pulse				0.55	mJ
E_{off}	turn-off energy per pulse				0.4	mJ
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15 \text{ V}; R_G = 68 \Omega; I_C = 30 \text{ A}$	$T_{VJ} = 125^\circ\text{C}$	$V_{CEK} \leq V_{CES} \cdot L_S \cdot d_I / dt$		V
I_{sc} (SCSOA)	short circuit safe operating area	$V_{CE} = 360 \text{ V}; V_{GE} = \pm 15 \text{ V}; R_G = 68 \Omega; t_p = 10 \mu\text{s}$	$T_{VJ} = 125^\circ\text{C}$	65		A
R_{thJC}	thermal resistance junction to case	(per IGBT)			1.6	K/W
R_{thCH}	thermal resistance case to heatsink				0.55	K/W

Output Inverter D1 - D6

Ratings

Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 150^\circ\text{C}$			600	V
I_{F25}	forward current	$T_C = 25^\circ\text{C}$			37	A
I_{F80}		$T_C = 80^\circ\text{C}$			24	A
V_F	forward voltage	$I_F = 15 \text{ A}; V_{GE} = 0 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$	1.8	2.1	V
			$T_{VJ} = 125^\circ\text{C}$	1.3		V
Q_{rr}	reverse recovery charge	$T_{VJ} = 125^\circ\text{C}$ $V_R = 300 \text{ V}$ $di_F/dt = -380 \text{ A}/\mu\text{s}$ $I_F = 15 \text{ A}; V_{GE} = 0 \text{ V}$			0.58	μC
I_{RM}	max. reverse recovery current				11.5	A
t_{rr}	reverse recovery time				115	ns
E_{rec}	reverse recovery energy				50	μJ
R_{thJC}	thermal resistance junction to case	(per diode)			1.6	K/W
R_{thCH}	thermal resistance case to heatsink				0.55	K/W

 $T_C = 25^\circ\text{C}$ unless otherwise stated

IXYS reserves the right to change limits, test conditions and dimensions.

20070531a

Input Rectifier Bridge D8 - D11**Ratings**

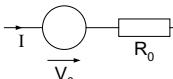
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V_{RRM}	max. repetitive reverse voltage		T _{VJ} = 25°C		1600	V
I_{FAV}	average forward current	sine 180°	T _C = 80°C		39	A
I_{DAVM}	max. average DC output current	rect.; d = 1/2	T _C = 80°C		42	A
I_{FSM}	max. forward surge current	t = 10 ms; sine 50 Hz	T _{VJ} = 25°C T _{VJ} = 125°C		550 tbd	A A
I²t	I ² t value for fusing	t = 10 ms; sine 50 Hz	T _{VJ} = 25°C T _{VJ} = 125°C		1270 tbd	A ² s A ² s
P_{tot}	total power dissipation		T _C = 25°C		100	W
V_F	forward voltage	I _F = 30 A	T _{VJ} = 25°C T _{VJ} = 125°C	1.2 1.3	1.5	V V
I_R	reverse current	V _R = V _{RRM}	T _{VJ} = 25°C T _{VJ} = 125°C	0.03 0.3	0.03	mA mA
R_{thJC}	thermal resistance junction to case	(per diode)			1.2	K/W
R_{thCH}	thermal resistance case to heatsink	(per diode)			0.4	K/W

Temperature Sensor NTC**Ratings**

Symbol	Definitions	Conditions	min.	typ.	max.	Unit
R₂₅	resistance		T _C = 25°C	4.75	5.0 3375	kΩ K
B_{25/50}						

Module**Ratings**

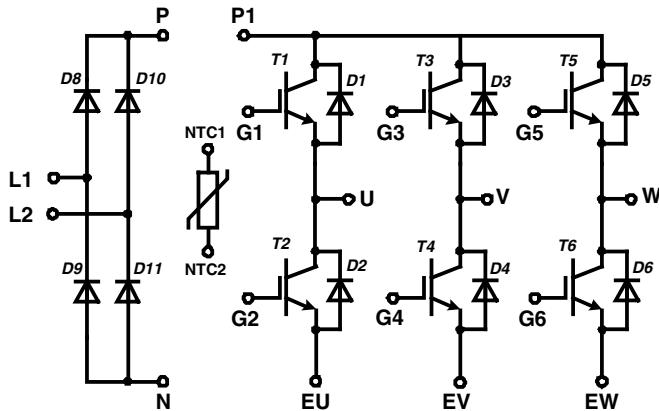
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
T_{VJ}	operating temperature		-40		125	°C
T_{VJM}	max. virtual junction temperature				150	°C
T_{stg}	storage temperature		-40		125	°C
V_{ISOL}	isolation voltage	I _{ISOL} ≤ 1 mA; 50/60 Hz			2500	V~
CTI	comparative tracking index			-		
F_c	mounting force		40		80	N
d_s	creep distance on surface		12.7			mm
d_A	strike distance through air		12			mm
Weight				35		g

Equivalent Circuits for Simulation**Ratings**

Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V₀	rectifier diode	D8 - D11	T _{VJ} = 125°C	0.9 6		V mΩ
R₀						
V₀	IGBT	T1 - T6	T _{VJ} = 125°C	1.15 77		V mΩ
R₀						
V₀	free wheeling diode	D1 - D6	T _{VJ} = 125°C	1.05 30		V mΩ
R₀						

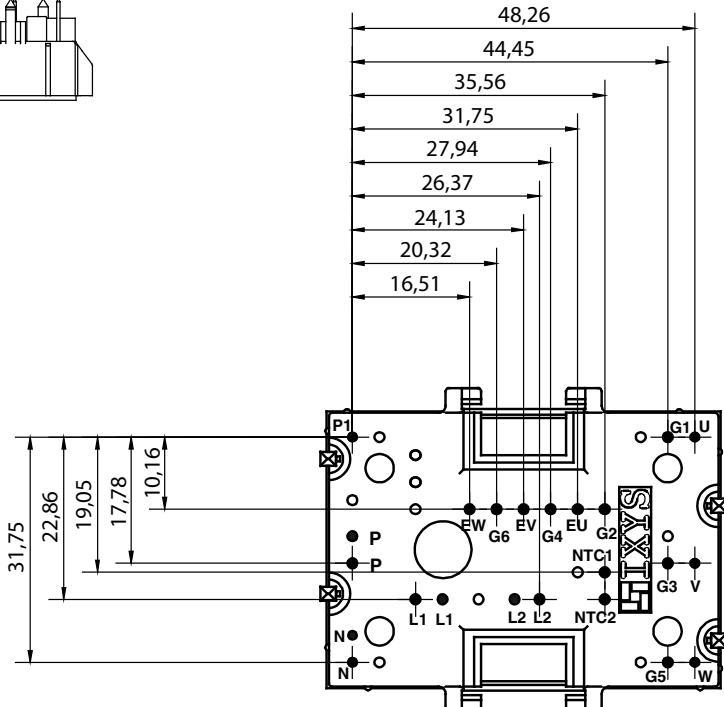
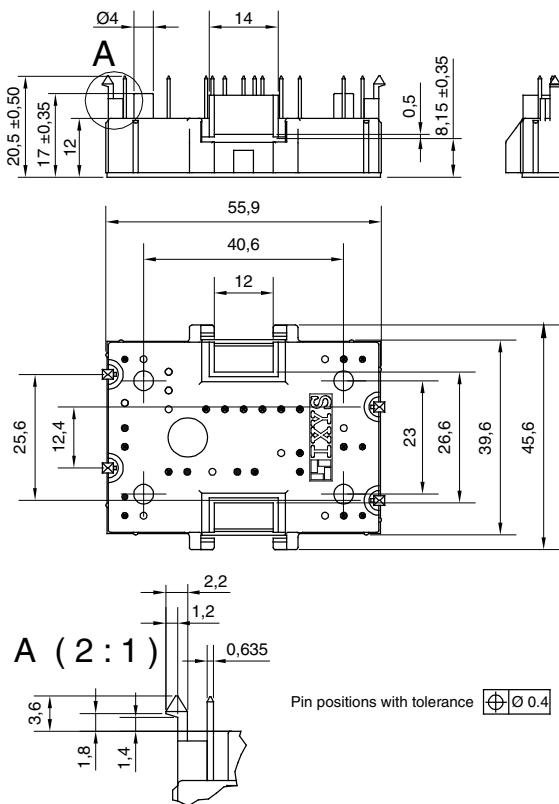
T_C = 25°C unless otherwise stated

Circuit Diagram

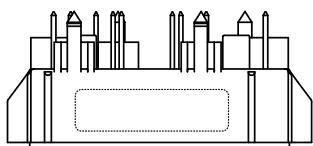


Outline Drawing

Dimensions in mm (1 mm = 0.0394")



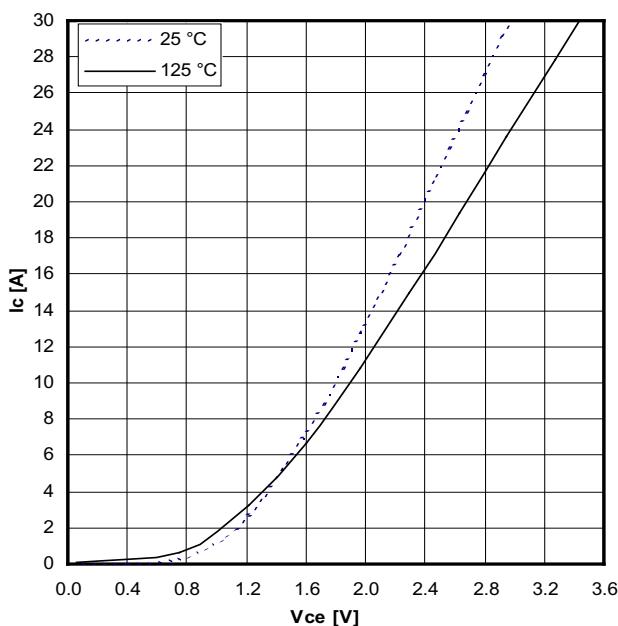
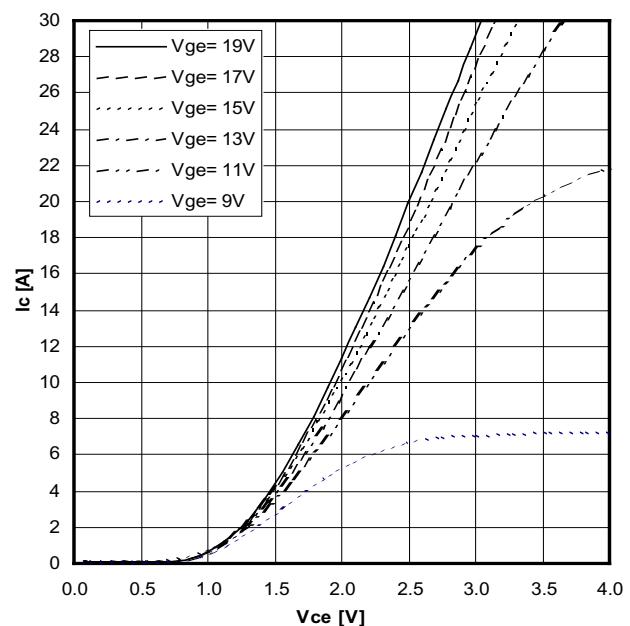
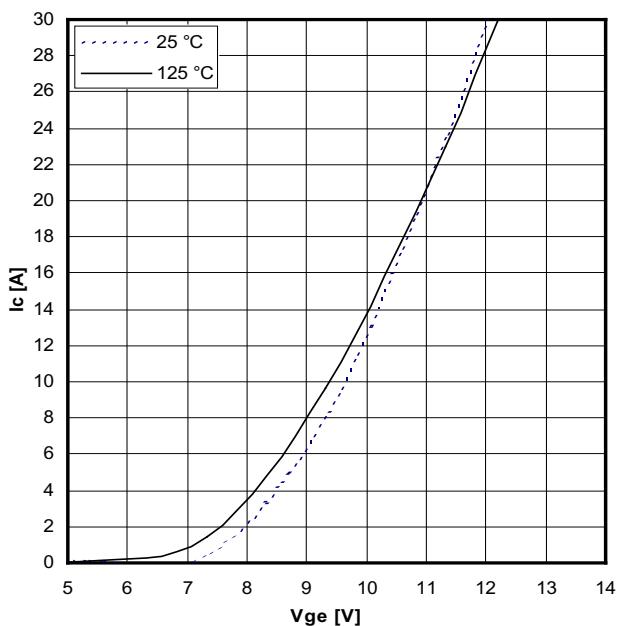
Product Marking



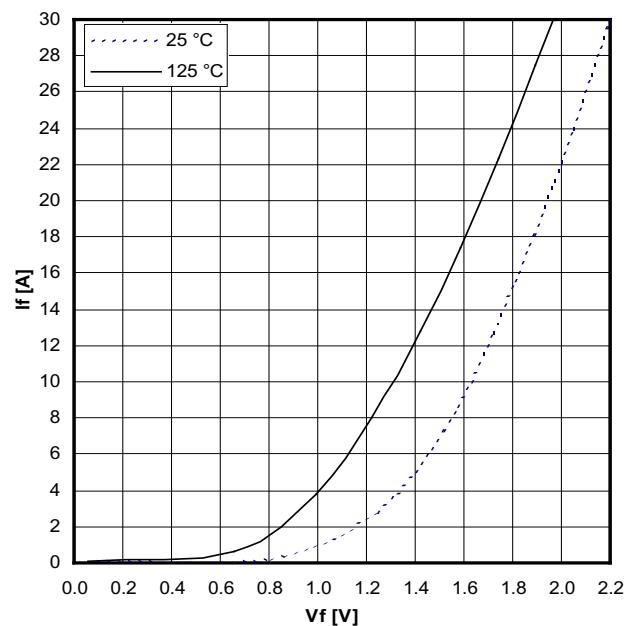
Part number

M = Module
 I = IGBT
 A = IGBT (NPT)
 A = Gen 1 / std
 15 = Current Rating [A]
 WD = 6-Pack + 1~ Rectifier Bridge
 600 = Reverse Voltage [V]
 T = NTC
 MH = MiniPack2

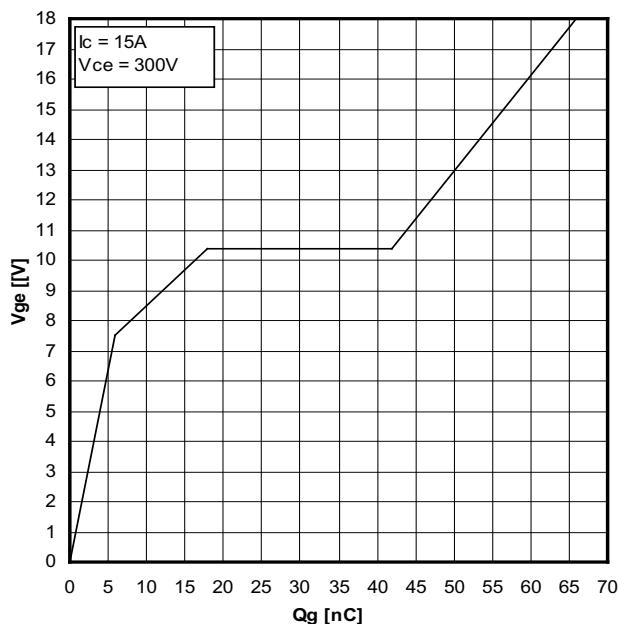
Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MIAA 15 WD 600 TMH	MIAA15WD600TMH	Box	20	504869

Typical output characteristics, $V_{GE} = 15$ VTypical output characteristics (125°C)

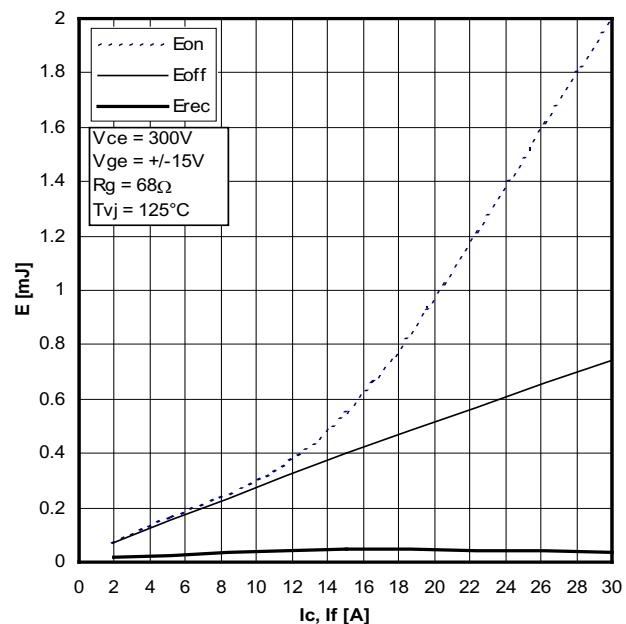
Typical transfer characteristics



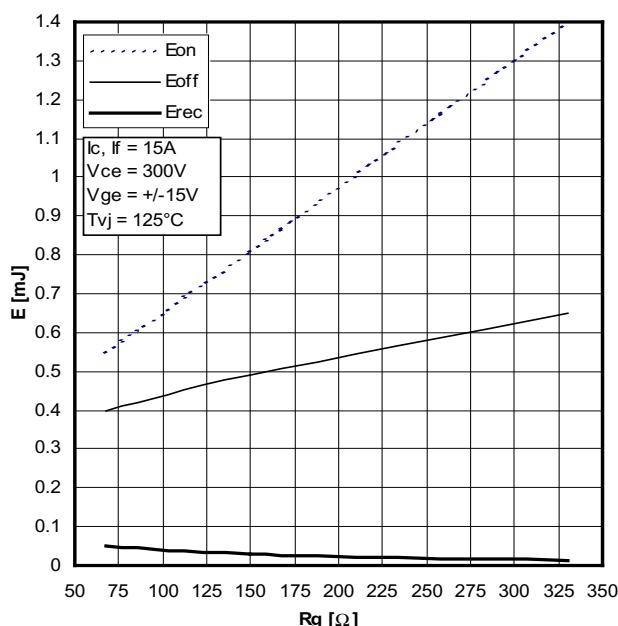
Typical forward characteristics of freewheeling diode



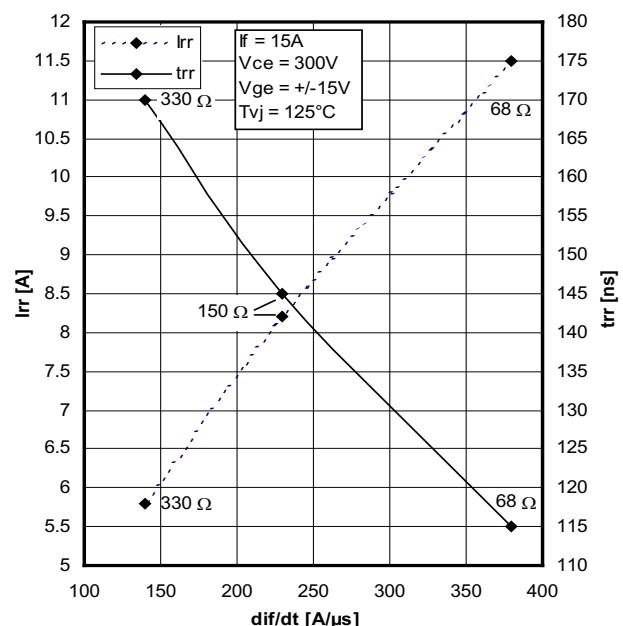
Typical turn on gate charge



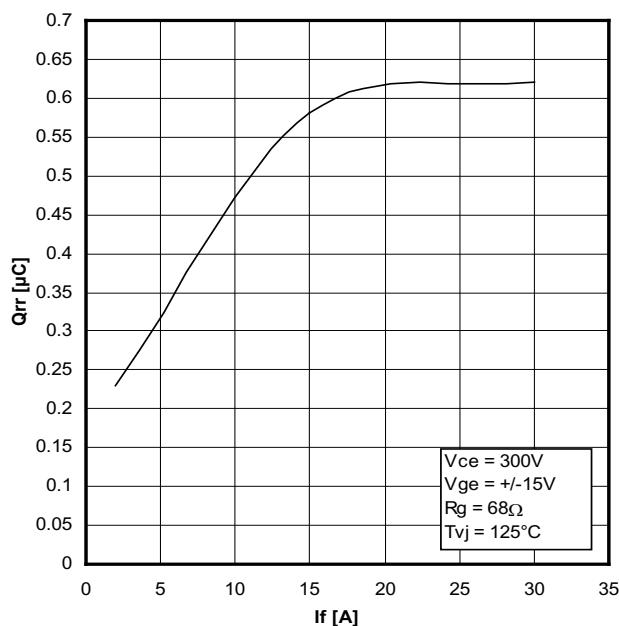
Typical switching energy versus collector current



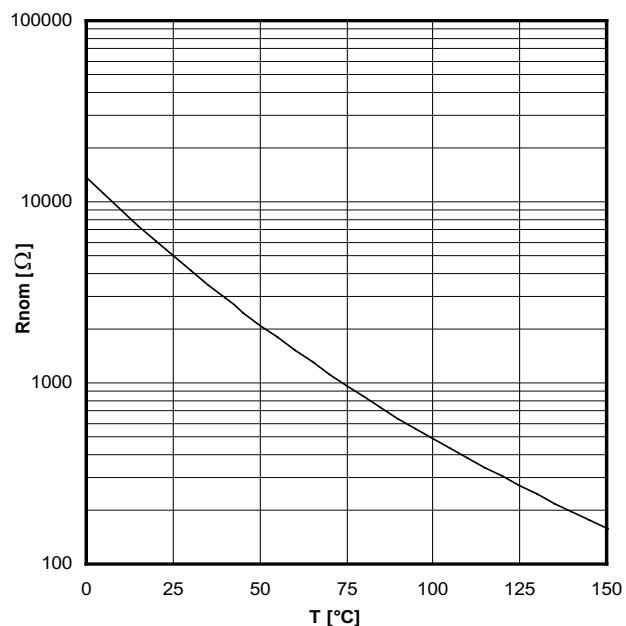
Typical switching energy versus gate resistance



Typical turn-off characteristics of free wheeling diode



Typical turn-off characteristics of free wheeling diode



Typical thermistor resistance versus temperature